L Number	Hits	Search Text	DB	Time stamp
1	994	gate same (work adj function)	USPAT	2002/07/31 14:59
2	781	(gate same (work adj function)) and transistor	USPAT	2002/07/31 14:56
3	717	((gate same (work adj function)) and transistor) and (thickness thick)	USPAT	2002/07/31 14:57
4	698	(((gate same (work adj function)) and transistor) and (thickness thick))	USPAT	2002/07/31 14:57
		and (conduct\$3 metal\$3)		,
5	1626	gate same (work adj function)	USPAT;	2002/07/31 15 03
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	1135	(gate same (work adj function)) and transistor	USPAT;	2002/07/31 15 00
		(See See Control of the Control of t	US-PGPUB;	2002/07/31 13 00
			EPO; JPO;	
			DERWENT;	
7	872	(tracta name (mark adi function)) and transistant and (distance distance	IBM_TDB	3003/08/31 15 03
,	0/2	((gate same (work adj function)) and transistor) and (thickness thick)	USPAT;	2002/07/31 15 02
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	832	(((gate same (work adj function)) and transistor) and (thickness thick))	USPAT;	2002/07/31 15:03
		and (conduct\$4 metal\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
9	832	((((gate same (work adj function)) and transistor) and (thickness thick))	USPAT;	2002/07/31 16.37
		and (conduct\$4 metal\$4)) and (work adj function)	US-PGPUB;	
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	i
. 10	600	(work adj function).ti.	USPAT;	2002/07/31 15:04
		( · · · · · · · · · · · · · · · · · · ·	US-PGPUB;	2002.07.51.15.01
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
11	21	(((((gate same (work adj function)) and transistor) and (thickness thick))	USPAT;	2002/07/31 15 04
		and (conduct\$4 metal\$4)) and (work adj function)) and ( (work adj	US-PGPUB;	2002/07/31 13 04
		function).ti.)		
		function).(i.)	EPO; JPO; DERWENT;	
12			IBM_TDB	. 2002/07/21 15 22
12	1		USPAT	2002/07/31 15.33
13	1		USPAT	2002/07/31 15 35
14	,		USPAT	2002/07/31 15 47
15	]	( (	USPAT	2002/07/31 15:55
16	1	( (work adj function).ti.) and critical adj thickness\$3	USPAT	2002/07/31 16 38
17	50	( (work adj function).ti.) and (first second)	USPAT	2002/07/31 17:04
18	1		USPAT	2002/07/31 16:43
19	1		USPAT	2002/07/31 16:49
20	0	"6051865".PN. and ((layer material) with work adj function)	USPAT	2002/07/31 17 05
21	0	"6051865".PN. and ((layer material) with (work adj function))	USPAT	2002/07/31 17 06
22	416	(((((gate same (work adj function)) and transistor) and (thickness thick))	USPAT	2002/07/31 17 08
		and (conduct\$4 metal\$4)) and (work adj function)) and ((layer material)		
		with (work adj function))		
23	92	((((((gate same (work adj function)) and transistor) and (thickness thick))	USPAT	2002/07/31 17 09
		and (conduct\$4 metal\$4)) and (work adj function)) and ((layer material)		
		with (work adj function))) and ((first second) with (work adj function))		
24	489	(((((gate same (work adj function)) and transistor) and (thickness thick))	USPAT;	2002/07/31 17 08
	.07	and (conduct\$4 metal\$4)) and (work adj function)) and ((layer material)	US-PGPUB;	
		with (work adj function))	EPO; JPO;	
		······· (······················)	DERWENT;	
			IBM_TDB	
	11 = 4	A company of the comp	.5	

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((((((gate same (work adj function)) and transistor) and (thickness thick)) and (conduct\$4 metal\$4)) and (work adj function)) and ((layer material) with (work adj function))) and ((first second) with (work adj function))

USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM\_TDB 2002/07/31 17:11